

IN THE CLAIMS

- 1 (Withdrawn). A method comprising:
forming a trench around an electrical component;
filling said trench with a conductive material; and
forming an interconnection layer coupled to said conductive material.
- 2 (Withdrawn). The method of claim 1 including forming said trench between said interconnection layer and a semiconductor structure.
- 3 (Withdrawn). The method of claim 1 including forming said trench between a pair of interconnection layers.
- 4 (Withdrawn). The method of claim 3 including forming a first trench between a first pair of interconnection layers and a second trench between a second pair of interconnection layers and positioning a passive circuit element between said trenches.
- 5 (Withdrawn). The method of claim 1 including grounding said material.
- 6 (Withdrawn). The method of claim 1 including positioning a passive circuit element within an enclosure formed by said material and layer.
- 7 (Withdrawn). The method of claim 6 including forming an opening in said material to allow an electrical connection to said passive circuit element.
- 8 (Withdrawn). The method of claim 6 including connecting said passive circuit element to other devices through a buried contact.
- 9 (Withdrawn). The method of claim 1 including electrically coupling said material and said interconnection layer.

10 (Withdrawn). The method of claim 6 including forming a flat spiral inductor to act as said passive circuit element over said semiconductor structure.

11 (Withdrawn). The method of claim 10 including forming a resistor and capacitor.

12 (Withdrawn). The method of claim 1 including forming said material over a guard ring.

13 (Original). An integrated circuit comprising:
a semiconductor substrate;
an interconnection layer positioned over said substrate;
a passive circuit element between said substrate and said interconnection layer;
and
a trench that encircles said passive circuit element, said trench filled with a conductive material.

14 (Original). The circuit of claim 13 wherein said trench substantially encircles said passive circuit element.

15 (Original). The circuit of claim 14 wherein said material includes an opening for an electrical connection to said passive circuit element.

16 (Original). The circuit of claim 13 wherein said passive circuit element is a flat spiral inductor.

17 (Original). The circuit of claim 13 including first, second and third interconnection layers, said passive circuit element formed in said second interconnection layer and a pair of metal-filled trenches extending between said first and second interconnection layers and said third and second interconnection layers.

18 (Original). The circuit of claim 13 wherein said trench extends from said interconnection layer to said substrate.

19 (Original). The circuit of claim 13 wherein said material is grounded.

20 (Original). The circuit of claim 13 including a buried contact which couples said passive circuit element under said material.

21 (Original). The circuit of claim 13 wherein said material and said interconnection layer are electrically coupled.

22 (Withdrawn). A method comprising:
forming an integrated passive circuit element; and
substantially enclosing said element using a trench filled with a conductive material.

23 (Withdrawn). The method of claim 22 including forming an interconnection layer coupled to said material.

24 (Currently Amended). An integrated circuit comprising:
a semiconductor substrate;
an active circuit element formed in said substrate;
a guard ring encircling said active circuit element formed in said substrate; and
a ~~trench filled with a~~ conductive material formed over and contacting ~~coupled to~~
said guard ring, said conductive material encircling said active circuit element.

25 (Original). The circuit of claim 23 wherein said material couples to a guard ring connection layer to bias said guard ring.

26 (Original). The circuit of claim 24 including a metal one layer over said substrate, said material electrically coupled to said guard ring and said metal one layer.

27 (Original). The circuit of claim 24 wherein said guard ring completely surrounds said active circuit element.

Claim 28 (Canceled).

29 (Original). The circuit of claim 24 wherein said active circuit element includes a transistor.

30 (Original). The circuit of claim 24 wherein said active circuit element is enclosed in a shield over the substrate, said shield formed by said material and an overlying metal layer.